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a first conductive layer across said first well and said second well in said surface of said semiconductor substrate with an end provided on said first well and another end provided on said second well, said first conductive layer electrically connecting said first well and said second well; and

a first contact electrically connected with said first well.

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B2

13. (Amended) A semiconductor device comprising:

a semiconductor substrate;

a first well of a prescribed conductivity type selectively formed in a surface of said semiconductor substrate and including a first active element;

a second well of the same conductivity type as said prescribed conductivity type selectively formed in a surface of said semiconductor substrate and including a second active element;

a conductive layer across said first well and said second well in said surface of said semiconductor substrate with an end provided on said first well and another end provided on said second well, said conductive layer including a compound layer of the material for said semiconductor substrate and a metal; and

a first contact electrically connected with said first well.

REMARKS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 1-14 are presently active in this case. Claims 1 and 13 have been amended by way of the present amendment.

In the outstanding Office Action, Claims 1 and 5-9 were rejected under 35 U.S.C. § 102(b) as being anticipated by U.S. Patent No. 5,843,813 to Wei et al.; Claims 1, 5, 10, 11,